

Sm₂NiSn₄: The intermediate structure type between ZrSi₂ and CeNiSi₂

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Abstract

A new rare earth nickel stannide, Sm₂NiSn₄, has been prepared by reacting the pure elements at high temperature in welded tantalum tubes. Its crystal structure was established by single crystal X-ray diffraction studies. Sm₂NiSn₄ crystallizes in the orthorhombic space group *Pnma* (No. 62) with cell parameters of $a = 16.878(2) \text{ \AA}$, $b = 4.4490(7) \text{ \AA}$, $c = 8.915(1) \text{ \AA}$, and $Z = 4$. Its structure can be viewed as the intermediate type between ZrSi₂ and CeNiSi₂. Sm₂NiSn₄ features two-dimensional (2D) corrugated [NiSn₄]⁶⁻ layers in which the 1D Sn zigzag chains and the 2D Sn square sheets are bridged by Ni atoms. The Sm³⁺ cations are located at the interlayer space. Results of both resistivity measurements and extended-Hückel tight-binding band structure calculations indicate that Sm₂NiSn₄ is metallic.

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1. Introduction

Intermetallic phases formed between alkali earth metal (or alkali metal or rare earth metal) and tin element are of great research interest due to their richness in structural chemistry and tunable electronic properties [1]. Phase diagram studies indicate that the Ca–Sn system alone exhibits seven intermediate phases [2,3]. Several types of anionic tin oligomers have also been found in these binary and ternary phases [2,4]. Mixing two types of cations with different sizes such as the combination of alkali earth and alkali metals, or two different alkali metals or two different alkali earth metals affords a number of polar intermetallics with unusual anionic clusters, chains and layers [5–8]. The tin-rich binary or ternary phases are also capable of forming type I clathrates featuring cages based on tin pentagons and possessing interesting transport properties [9].

The Pauling's electronegativities of Cu (1.90) and Ni (1.91) are very close to that of Sn (1.96), hence it is expected that a variety of *A*–Cu(Ni)–Sn (*A* is alkali earth, alkali or rare earth metal) ternary phases with strong covalent

Cu(Ni)–Sn bonding can be formed. Furthermore, the introduction of the transition metals in these systems can also dramatically change the electronic and magnetic properties of the resultant intermetallic compounds as well as improve their thermal stabilities [1]. Rare earth copper stannides have been widely investigated due to their interesting magnetic and transport properties [10]. It is recently reported that the structure of Ca₆Cu₂Sn₇ features a novel three dimensional (3D) open framework built from [Cu₂Sn₃] layers cross-linked by novel zigzag [Sn₄] tetramers [11]. As for the Ae–Ni–Sn system, a few phases reported include BaNiSn₃, Mg_{11.92}Ni_{2.32}Sn_{1.76}, MgNi₂Sn and Ca₇Ni₄Sn₁₃ [12]. It is interesting to mention that Ca₇Ni₄Sn₁₃ features a interesting 3D anionic network formed by 1D condensed chains of “drum”-like [Ni₄Sn₄Sn_{8/2}] clusters interconnected by square planar [Sn₃] units via *exo*-bonds was reported [12d]. A large number of rare earth nickel tin ternary phases have been isolated [13–19]. A few such compounds belong to the RENi_{1-x}Sn₂ family with the CeNiSi₂ structure type, the nickel site is normally partially occupied with the *I*–*x* value in the range of 0.08–0.74 [13]. It also should be mentioned that LuNiSn₂ and DyNiSn₂ are not of the CeNiSi₂ structure type, but they form a new structure type which features Ni₂Sn₃ five member rings [14]. Besides some

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nickel-rich ternary phases, other rare earth nickel tin ternary compounds reported include RENiSn with the TiNiSi structure type [15], CeNi₂Sn₂ in the CeAl₂Ga₂ structure type [16], Lu₂NiSn₆ featuring layers of [NiSn₄] and 1D zigzag chains of 2-bonded Sn atoms and LuNiSn₄ composed of [NiSn₃] layers and 1D zigzag chains of 2-bonded Sn atoms [17], Ce₃Ni₂Sn₇ in the La₃Co₂Sn₇ structure [18], La_{4.87}Ni₁₂Sn₂₄ and Gd₃Ni₈Sn_{16.33} [19]. Our attempts to prepare the rare earth nickel analogs of Ca₆Cu₂Sn₇ led to the discovery of a novel polar intermetallic phase, Sm₂NiSn₄. Its structure can be viewed as the intermediate type between ZrSi₂ and CeNiSi₂ structure types [13,20]. Herein, we report its syntheses, crystal structures, band structures, and physical properties.

2. Experimental section

2.1. Materials and instrumentation

All manipulations were performed inside an argon-filled glove box with moisture level below 1 ppm. The starting materials are samarium pieces (99.98%, Alfa-Aesar), nickel powder (99.999%, Tianjin Fuchen chemical reagent company), and tin granules (99.8%, Shanghai fourth chemical reagent company). DC magnetic measurement was performed on a PPMS-9T magnetometer at a field of 5000 Oe in the temperature range of 2–300 K. The resistivity measurements were performed on an Oxford Mablal-12 magnetometer by using a standard four-probe technique in the temperature range of 6–300 K. An energy dispersive X-ray spectroscope (EDS, Oxford INCA) analysis attached to the FESEM was used to analyze the elemental composition. X-ray powder diffraction patterns were collected on an X'Pert-Pro diffractometer using CuK α radiation ($\lambda = 1.5406 \text{ \AA}$) in the 2θ range of 5–85°. The generator voltage is 45 kV and the tube current is 40 mA.

2.2. Syntheses of Sm₂NiSn₄

Single crystals of Sm₂NiSn₄ was initially obtained by reacting a mixture composed of Sm, Ni, and Sn in a molar ratio of 6:2:7 at 950 °C, in our attempts to prepare Sm₆Ni₂Sn₇, which could be an analog of Ca₆Cu₂Sn₇ [9]. A mixture of Sm (225.5 mg, 1.5 mmol), Ni (29.4 mg, 0.5 mmol) and Sn (209.3 mg, 1.75 mmol) was loaded into a niobium tube, which was subsequently arc-welded under an argon atmosphere and put into an evacuated quartz tube. The sample was allowed to heat at 950 °C for 5 days with prior heating under dynamic vacuum at 300 °C for 1 day. Then it was allowed to cool slowly (15 °C/h) to room temperature. Single crystals of Sm₂NiSn₄ (gray, plate-shaped) were obtained in low yield. Several single crystals were used for the microprobe elemental analyses. The measured chemical composition, Sm_{1.92}Ni_{0.88}Sn_{4.0}, is very close to the structurally refined one. After proper structural analyses, Sm₂NiSn₄ was prepared quantitatively by the reactions of the stoichiometric mixtures of the pure metals

in Ta tubes at 970 °C for 36 h, quenched in water and annealed at 700 °C for 15 days. Sm₂NiSn₄ is air-stable and its purity was confirmed by X-ray powder diffraction studies (see Supporting Information). The use of the Ta tubes instead of the Nb tubes is to eliminate Nb₃Sn impurity found in the products when Nb tubes were used. Attempts to prepare other RE₂NiSn₄ analogies (RE = La, Gd, Yb) were tried but unsuccessful.

2.3. Crystal structure determination

A single crystal of Sm₂NiSn₄ (size: 0.15 × 0.08 × 0.05 mm³) was selected from the reaction products and sealed into a thin-walled glass capillary under an argon atmosphere. Data collection was performed on a Rigaku Mercury CCD (MoK α radiation, graphite monochromator) at 293(2) K. The data set was corrected for Lorentz factor, polarization, air absorption and absorption due to variations in the path length through the detector faceplate. Absorption correction based on Multi-scan method was also applied [21a].

The structure of Sm₂NiSn₄ was solved by using direct methods (SHELXTL) and refined by least-squares methods with atomic coordinates and anisotropic thermal parameters [21b]. Based on systematic absences and *E*-value statistics, two space groups, *Pnma* and *Pna2*₁ are possible for Sm₂NiSn₄, of which the centrosymmetric one gave a satisfactory refinement. All atomic sites in Sm₂NiSn₄ are fully occupied according to the site occupancy refinements and no abnormal behavior was found for their thermal parameters. Final difference Fourier maps showed featureless residual peaks of 2.29 and –2.28 e \AA^{-3} (0.71 and 1.45 \AA from Sn(2) and Sn(1), respectively). Crystallographic data and structural refinements are summarized in Table 1. Atomic coordinates, and selected bond lengths and angles are listed in Tables 2 and 3, respectively. More details about crystallographic studies are given as the Supporting Information. Crystallographic data in CIF format for Sm₂NiSn₄ has been deposited as CSD number 416584. These data may be obtained free of charge by contacting FIZ Karlsruhe at +49 7247 808 666 (fax) or crysddata@fiz-karlsruhe.de (email).

2.4. Extended hückel band calculations

Three-dimensional band structure calculations for Sm₂NiSn₄ along with the density of states (DOS) and crystal orbital overlap population (COOP) curves were performed by using the Crystal and Electronic Structure Analyzer (CAESAR) software package [22]. The following atomic orbital energies were employed for the calculations: Sm 6s –4.86, 6p –4.86, 5d –6.06, 4f –11.28; Ni 4s –9.17, 4p –5.15, 3d –13.49; Sn 5s –16.16, 5p –8.32 eV.

3. Results and discussion

Both ZrSi₂ and CeNiSi₂ crystallize in orthorhombic *Cmcm* [20,23]. Comparing the cell parameters of the

Table 1
Summary of cell parameters, data collection and structure refinements for Sm_2NiSn_4

Empirical formula	Sm_2NiSn_4
fw	1198.39
Space group	$Pnma$ (No. 62)
A , Å	16.878(2)
B , Å	4.4490(7)
C , Å	8.915(1)
V , Å ³	669.4(2)
Z	4
D_{calcd} , g cm ⁻³	8.277
Temp, K	293(2)
μ , mm ⁻¹	34.544
Size (mm)	0.15 × 0.08 × 0.05
Color and habit	gray, plate
hkl range	(−21, 20), ±5, (−10, 11)
Reflections collected	4849
Unique reflections	861 ($R_{\text{int}} = 0.0416$)
Reflections ($I > 2\sigma(I)$)	781
GOF on F^2	1.057
R_1 , wR_2 ($I > 2\sigma(I)$) ^a	0.0261/0.0680
R_1 , wR_2 (all data)	0.0318/0.0707

$$R_1 = \sum ||F_o| - |F_c|| / \sum |F_o|, wR_2 = \sum w[(F_o)^2 - (F_c)^2]^2 / \sum w[(F_o)^2]^{1/2}.$$

Table 2
Atomic coordinates and $U(\text{eq}) (\times 10^3 \text{Å}^2)$ for Sm_2NiSn_4

Atom	Wyck.	x	y	z	U_{eq}
Sm(1)	4c	0.14807(3)	1/4	0.36580(5)	4(1)
Sm(2)	4c	0.35292(3)	3/4	0.39035(6)	5(1)
Ni(1)	4c	0.06200(9)	3/4	0.1438(1)	12(1)
Sn(1)	4c	0.32411(5)	1/4	0.12728(6)	8(1)
Sn(2)	4c	0.29041(5)	1/4	0.62914(6)	7(1)
Sn(3)	4c	0.99184(5)	1/4	0.12994(6)	7(1)
Sn(4)	4c	0.99180(5)	3/4	0.39000(7)	8(1)

CeNiSi_2 and Sm_2NiSn_4 , it is noticed that $a_{\text{Sm}_2\text{NiSn}_4} \approx b_{\text{CeNiSi}_2}$, $c_{\text{Sm}_2\text{NiSn}_4} \approx 2a_{\text{CeNiSi}_2}$ and $b_{\text{Sm}_2\text{NiSn}_4} \approx c_{\text{CeNiSi}_2}$. Since Sm_2NiSn_4 crystallizes in orthorhombic $Pnma$ which is primitive, hence Sm_2NiSn_4 forms a different structure type from those of ZrSi_2 and CeNiSi_2 .

The structure of Sm_2NiSn_4 features a 2D $[\text{NiSn}_4]$ layer composed of Sn square sheet and zigzag Sn chains that are bridged by nickel atoms (Fig. 1). Such structure type is the intermediate version between ZrSi_2 and CeNiSi_2 .

The 2D Sn square sheet is formed by Sn(3) and Sn(4) atoms (Fig. 2a). Half of the Sn_4 squares within the square sheet are capped by Ni atoms alternatively on both sides, resulting in $[\text{NiSn}_2]$ layers. Within the $[\text{NiSn}_2]$ layer, the distance from Ni(1) to the Sn_4 square is 1.123 Å. Such connectivity results in also 1D $[\text{NiSn}]$ “ladder” composed of Ni(1) and Sn(3) along the b -axis, and these ladders are further bridged by Sn(4) atoms into a 2D architecture (Fig. 2a). It is interesting to note that such $[\text{NiSn}]$ “ladder” is very similar to the $[\text{CuSn}]$ one in $\text{Ca}_6\text{Cu}_2\text{Sn}_7$ (Fig. 2b) [11]. Within the $[\text{NiSn}_2]$ layer, three types of Sn–Sn bonds are found: Sn(4)–Sn(4) (2.9785(9) Å) for the vacant $[\text{Sn}_4]$ square composed of one Sn(3) and three Sn(4) atoms,

Table 3
Selected bond lengths (Å) and angles for Sm_2NiSn_4

Sm(1)–Sn(2)	3.2369(6) × 2	Sm(1)–Sn(1)	3.2561(6) × 2
Sm(1)–Sn(2)	3.3590(8)	Sm(1)–Sn(3)	3.3725(9)
Sm(1)–Sn(4)	3.4571(9) × 2	Sm(1)–Sn(1)	3.6537(9)
Sm(1)–Ni(1)	3.313(1) × 2	Sm(2)–Sn(3)	3.2371(8) × 2
Sm(2)–Sn(2)	3.2546(6) × 2	Sm(2)–Sn(1)	3.2687(6) × 2
Sm(2)–Sn(2)	3.3578(9)	Sm(2)–Sn(3)	3.3804(9)
Sm(2)–Sn(4)	3.4264(9)	Sm(2)–Ni(1)	3.481(1) × 2
Sm(2)–Ni(1)	3.542(2)	Ni(1)–Sn(4)	2.494(2)
Ni(1)–Sn(2)	2.494(2)	Ni(1)–Sn(3)	2.5231(9) × 2
Ni(1)–Sn(3)	2.604(2)	Sn(1)–Sn(2)	2.9470(8) × 2
Sn(3)–Sn(4)	3.2130(7) × 2	Sn(3)–Sn(3)	3.2236(9) × 2
Sn(4)–Sn(4)	2.9785(9) × 2		
Sn(4)–Ni(1)–Sn(2)	121.38(6)	Sn(4)–Ni(1)–Sn(3)	79.64(4) × 2
Sn(2)–Ni(1)–Sn(3)	117.78(3) × 2	Sn(3)–Ni(1)–Sn(3)	123.68(7)
Sn(4)–Ni(1)–Sn(3)	131.21(7)	Sn(2)–Ni(1)–Sn(3)	107.42(5)
Sn(3)–Ni(1)–Sn(3)	77.89(3) × 2	Ni(1)–Sn(4)–Sn(3)	50.58(2) × 2
Ni(1)–Sn(2)–Sn(1)	130.94(2) × 2	Ni(1)–Sn(3)–Ni(1)	123.68(7)
Ni(1)–Sn(3)–Ni(1)	102.11(3) × 2	Ni(1)–Sn(3)–Sn(4)	49.78(3) × 2
Ni(1)–Sn(3)–Sn(4)	125.11(4) × 2	Ni(1)–Sn(3)–Sn(4)	132.54(2) × 2
Ni(1)–Sn(3)–Sn(3)	52.17(3) × 2	Ni(1)–Sn(3)–Sn(3)	49.93(2) × 2
Ni(1)–Sn(3)–Sn(3)	127.12(4)	Ni(1)–Sn(4)–Sn(4)	122.36(4) × 2
Sn(4)–Sn(3)–Sn(3)	175.11(5) × 2	Sn(4)–Sn(3)–Sn(3)	92.34(2) × 2
Sn(3)–Sn(3)–Sn(3)	87.27(3)	Sn(2)–Sn(1)–Sn(2)	98.02(3) × 2
Sn(4)–Sn(4)–Sn(4)	96.64(4)	Sn(4)–Sn(3)–Sn(4)	87.63(2)
Sn(4)–Sn(4)–Sn(3)	172.83(4) × 2	Sn(4)–Sn(4)–Sn(3)	87.59(2) × 2
Sn(3)–Sn(4)–Sn(3)	87.63(2)		

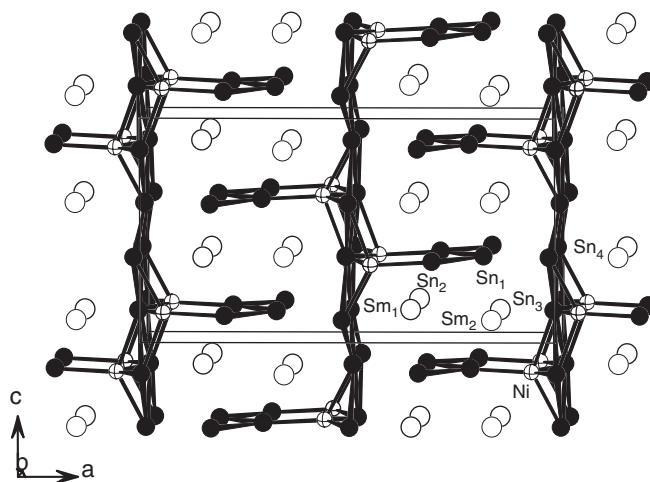


Fig. 1. View of the structure of Sm_2NiSn_4 down the b -axis.

Sn(3)–Sn(3) (3.2236(9) Å) for the Ni-capped $[\text{Sn}_4]$ square, and Sn(3)–Sn(4) (3.2130(7) Å) which is shared by the above two types of squares. The Sn(4)–Sn(4) distance is significantly longer than the Sn–Sn single bond distance of 2.81 Å in the diamond modification of α -Sn [24]. The Ni–Sn distances fall in the range of 2.494(2)–2.604(2) Å, which are comparable with those in other rare earth nickel tin compounds [13–19]. It should be noted that the $[\text{NiSn}_2]$ layer in Sm_2NiSn_4 is somehow similar to the $[\text{Cu}_2\text{Sn}_3]$ layer in $\text{Ca}_6\text{Cu}_2\text{Sn}_7$ and the $[\text{NiSi}]$ layer in CeNiSi_2 (Fig. 2) [11,23]. All of them feature a square sheet of tetrels (Si or Sn) capped by transition metals (Ni or Cu) alternatively

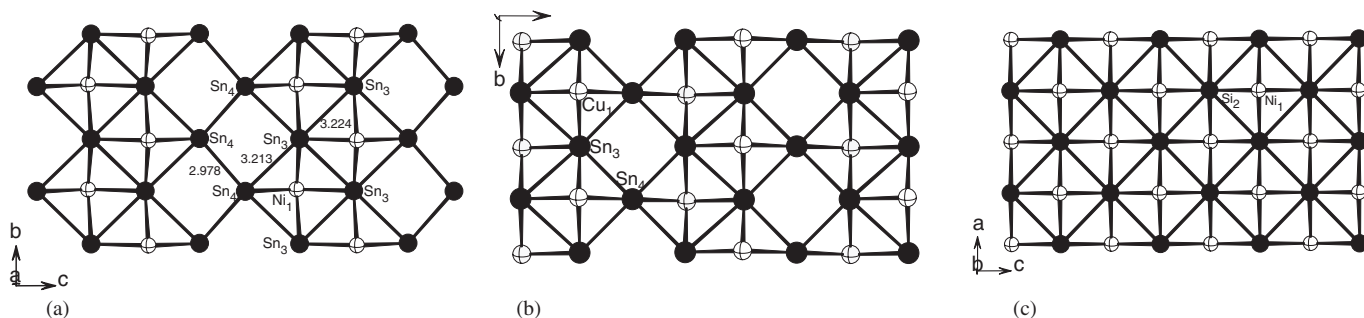


Fig. 2. Comparison of the [NiSn₂] layer in Sm₂NiSn₄ (a) with the [Cu₂Sn₃] layer in Ca₆Cu₂Sn₇ (b), and the [NiSi] layer in CeNiSi₂ (c).

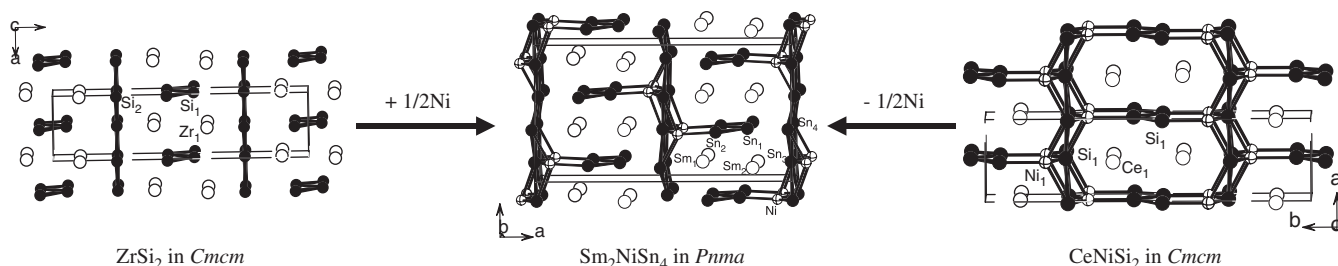


Fig. 3. Comparison of the structure of Sm₂NiSn₄ with those of ZrSi₂ and CeNiSi₂.

above and below. There are no vacant Si₄ squares in the [NiSi] layer, whereas half and one-third Sn₄ squares are vacant in the [NiSn₂] and [Cu₂Sn₃] layers, respectively (Fig. 2).

The zigzag Sn chain is formed by Sn(1) and Sn(2) atoms (Fig. 1), similar such tin chains can be found in Lu₂NiSn₆, LuNiSn₄, ThSn₂ and AECuSn₂ (AE = Sr, Ba) [17,25]. The Sn–Sn distance of 2.9470(8) Å is comparable to that in SrSn (2.924 Å) [26]. The Sn–Sn–Sn angle is 98.02(3)°, which is much smaller than that for an ideal tetrahedral geometry due to the presence of the lone pair electrons.

The above two types of building units in Sm₂NiSn₄ are further interlinked via Ni–Sn bonds (2.494(2) Å) into [NiSn₄] layers (Fig. 1). Such [NiSn₄] layer can also be viewed as being formed by [NiSn₂] layer attached by 1D zigzag Sn chains alternatively on both sides. The shortest interlayer Sn...Sn separation is 3.603 Å. The Sm³⁺ cations are located at the interlayer space. Sm(1) is 11-coordinated by two Ni and nine Sn atoms, whereas Sm(2) is surrounded by three Ni and ten Sn atoms. The Sm–Ni and Sm–Sn distances are in the ranges of 3.313(1)–3.542(2) Å and 3.2369(6)–3.6537(9) Å, respectively. The Ni atom is in a distorted [Sn₅] square pyramidal geometry. The Sn–Ni–Sn angles are in the range of 77.89(3) and 121.38(6)°.

It is very interesting to note that the structure of Sm₂NiSn₄ is closely related to the ZrSi₂ and CeNiSi₂ structure types [20,23]. As shown in Fig. 3, all three structures are based on 2D tetrel (Si or Sn) square sheets and 1D zigzag tetrel chains. The square sheets and the zigzag chains remain isolated in ZrSi₂. In CeNiSi₂, the silicon square sheets and zigzag chains are bridged by Ni

atoms into a 3D open framework. As for Sm₂NiSn₄, the tin chains are only hanging on both sides of the [NiSn₂] layer due to the lack of 50% Ni atoms compared with CeNiSi₂. Hence Sm₂NiSn₄ serves as an intermediate version between ZrSi₂ and CeNiSi₂ structural types. It should be mentioned that many phases in Ln–Ni–Sn system such as LaNi_{0.74}Sn₂ are nonstoichiometric and of the CeNiSi₂ structure type, in which the nickel site is only partially occupied [13].

It is also interesting to compare the structure of Sm₂NiSn₄ with those of Lu₂NiSn₆ and LuNiSn₄ [17]. All three compounds are composed of 2D tin square sheet with capping nickel atoms and 1D zigzag tin chains (Fig. 4). The 1D zigzag chains of tin in Sm₂NiSn₄ are bridged to the 2D tin square sheet through the capping nickel atoms whereas such 1D chains in Lu₂NiSn₆ and LuNiSn₄ are isolated. Furthermore, the nickel atom in Sm₂NiSn₄ is bonded to five tin atoms in a square pyramidal geometry whereas each nickel atom in Lu₂NiSn₆ and LuNiSn₄ is sandwich between two Sn₄ squares (Fig. 4), in other words, it is in the center of a Sn₈ cubane. Capping of the Ni atoms alternatively on both sides of the tin square sheet in Sm₂NiSn₄ resulted in the [NiSn₂] layers. The interconnection of the nickel atoms and two tin square sheets in Lu₂NiSn₆ forms [NiSn₄] double layers with the inter-sheet Sn–Sn distances of 3.151 and 3.216 Å, respectively (Fig. 4b). These inter sheet Sn–Sn bonds are slightly longer than those for the Sn₄ square (3.050 Å) [17]. In LuNiSn₄, three tin square sheets and the nickel atoms are interconnected into a [NiSn₃] triple layers (Fig. 4c), and the Sn–Sn distances between two neighboring square sheets are 2.914 and 2.954 Å, respectively, which are slightly shorter than the Sn–Sn bonds within the tin square

(3.083 Å) [17]. The shortest Sn...Sn separations between the 1D tin chain and 2D nickel-tin layer are 3.563 and 3.654 Å, respectively, for Lu_2NiSn_6 and LuNiSn_4 .

To obtain further insights into the chemical bonding of Sm_2NiSn_4 , three dimensional band structure calculations were performed by using the semi-empirical extended Hückel methods [22]. Sm_2NiSn_4 is metallic with no band gap around the Fermi level (Fig. 5). The states just below and above the Fermi level are mainly from p orbitals of Sn atoms, mixing with small amount of s and p orbitals of Ni atoms, as well as small amount of s and p contributions from Sm atoms. The two peaks in the DOS, observed

around the Fermi level and -2.0 eV, are the results of splitting of Sm f and Ni d states due to spin-orbit interactions, respectively. E_F suggests that Sm f states are partially occupied. This indicates the f^5 electron configuration corresponding to Sm^{3+} , which is in agreement with the results of magnetic measurements. However, the Ni d orbitals are almost fully occupied with electrons below the Fermi level, indicating a reduced state for Ni(1) atom. This is reasonable, as is well known that, in many intermetallic phases containing late transition metals with high electronegativity, band structure calculations suggest the transition metals are effectively in neutral or negative oxidation states [11,27]. Semi-empirical COOP allows a more quantitative bond analysis. The Sn–Sn bond (2.9470(8) Å) of the zigzag Sn chain has an overlap population (OP) value of 0.274, which is much stronger than the Sn–Sn bonds (average OP = 0.174) of the $[\text{NiSn}_2]$ layer. The Ni–Sn bonds (2.494–2.604 Å) with an average OP value of 0.345 are significant bonding. The Sm–Sn (3.2369(6)–3.6537(9) Å) and Sm–Ni (3.313(1)–3.542(2) Å) bonds with small OP values of 0.049 and 0.022, respectively, are very weak bonding.

The magnetic susceptibility of Sm_2NiSn_4 measured in the range of 2–300 K, is shown in Fig. 6a. It does not obey the Curie–Weiss law over the entire experimental temperature region. The sharp maximum of the χ_M – T plot at 17 K indicates that it undergoes an antiferromagnetic ordering transition at low temperature. The calculated effective moment μ_{eff} is $1.81 \mu_B/\text{Sm-atom}$ at 300 K, which is slightly higher than the theoretical values of $1.66 \mu_B$ for one Sm^{3+} ion per formula based on the Van Vleck formula [28]. Resistivity measurements reveal a metallic behavior for Sm_2NiSn_4 with $\rho_{298} = 75.5 \mu\Omega\text{cm}$ and $\rho_6 = 53.7 \mu\Omega\text{cm}$, respectively (Fig. 6b). There is an obvious transition near the Néel temperature (ca. 17 K), which is in good agreement with the magnetic data. These values are comparable to those for $\text{RE}_9\text{Ni}_{24}\text{Sn}_{49}$ phases ($\text{RE} = \text{Y}, \text{Ce}, \text{Pr}, \text{Sm}$ and Tb) [29].

In summary, we have obtained a novel rare earth tin-rich ternary phase Sm_2NiSn_4 . The structure of Sm_2NiSn_4 features a 2D anionic $[\text{NiSn}_4]$ layer in which 1D Sn zigzag

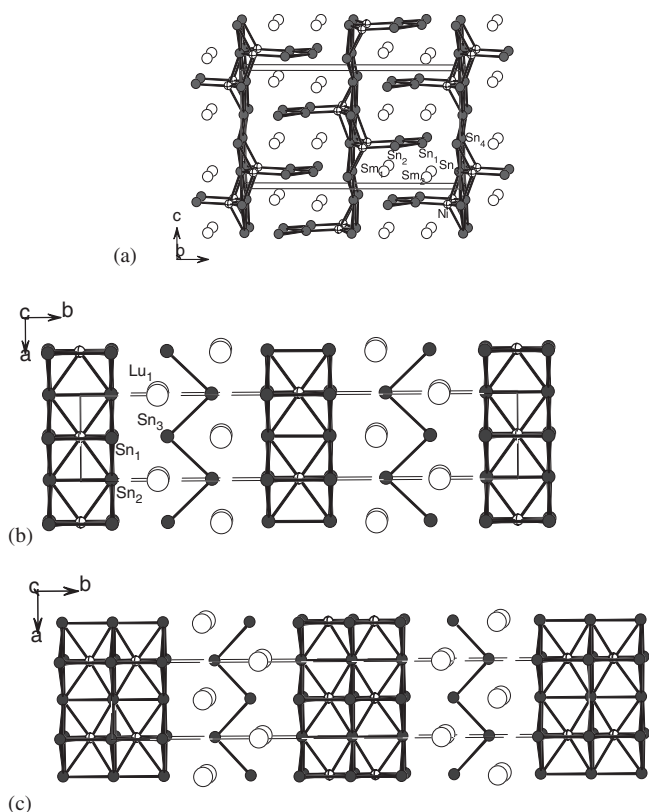


Fig. 4. Comparison of the structure of Sm_2NiSn_4 (a) with those of Lu_2NiSn_6 (b) and LuNiSn_4 (c).

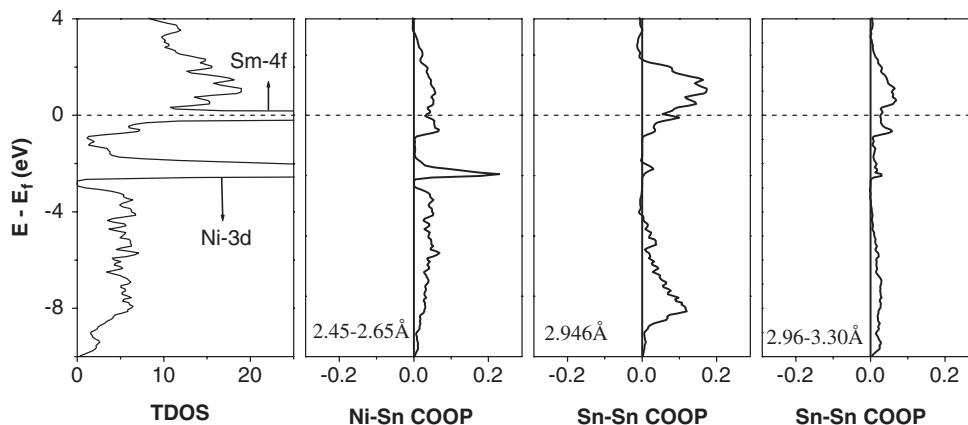


Fig. 5. DOS and COOP curves for Sm_2NiSn_4 . The Fermi level is represented by the dotted line and is set at 0 eV.

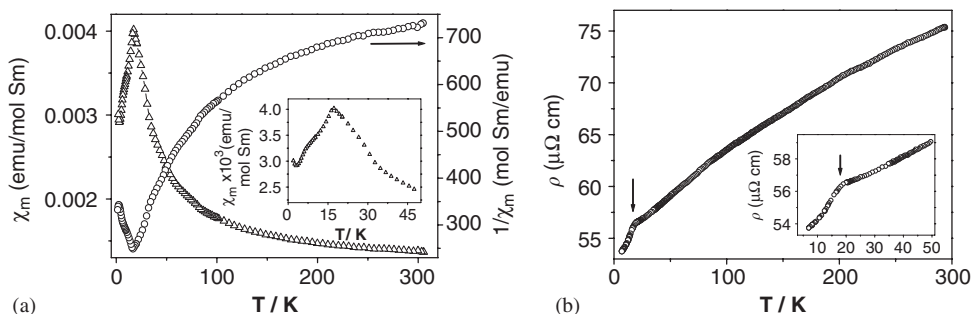


Fig. 6. χ_m and χ_m^{-1} versus T plots (a) and the dependences of ρ with temperature for Sm_2NiSn_4 (b). The inset shows magnified view at low temperatures.

chains and 2D Sn square sheets are interconnected by bridging Ni atoms. It is the intermediate type between ZrSi_2 and CeNiSi_2 . Sm_2NiSn_4 is metallic based on band structure calculation as well as resistivity measurements.

4. Supporting information available

Figures showing the coordination geometries around Sm, Sn and Ni atoms, lists of atomic displacement parameters, simulated and experimental XRD powder patterns.

Acknowledgments

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Appendix A. Supplementary materials

Supplementary data associated with this article can be found in the online version at [doi:10.1016/j.jssc.2006.07.002](https://doi.org/10.1016/j.jssc.2006.07.002).

References

- [1] (a) B. Eisenmann, G. Cordier, *Chemistry, Structure and Bonding of Zintl Phases and Ions*, VCH Publishers, New York, 1996, p. 61; (b) J.D. Corbett, *Chemistry, Structure and Bonding of Zintl Phases and Ions*, VCH Publishers, New York, 1996, p.139; (c) J.D. Corbett, *Angew. Chem. Int. Ed.* 39 (2000) 670.
- [2] (a) A. Palenzona, P. Manfrinetti, M.L. Fornasini, *J. Alloys Compd.* 312 (2000) 165; (b) E. Zintl, *S. Neumayr, Z. Elektrochem.* 39 (1933) 86; (c) P. Eckerlin, H.J. Meyer, E. Wölfel, *Z. Anorg. Allg. Chem.* 281 (1955) 322; (d) A.K. Ganguli, A.M. Guloy, E.A. Leon-Escamilla, J.D. Corbett, *Inorg. Chem.* 32 (1993) 4349.
- [3] (a) A.M. Guloy, J.D. Corbett, *Z. Anorg. Allg. Chem.* 616 (1992) 61; (b) E.A. Leon-Escamilla, J.D. Corbett, *J. Alloys Compd.* 265 (1998) 104; (c) P. Eckerlin, E. Leicht, E. Wölfel, *Z. Anorg. Allg. Chem.* 307 (1961) 145.
- [4] E.A. Leon-Escamilla, J.D. Corbett, *Inorg. Chem.* 38 (1999) 738.
- [5] (a) I. Todorov, S.C. Sevov, *Inorg. Chem.* 43 (2004) 6490; (b) S. Bobev, S.C. Sevov, *J. Alloy Compd.* 338 (2002) 87; (c) S. Bobev, S.C. Sevov, *J. Am. Chem. Soc.* 124 (2002) 3359; (d) S. Bobev, S.C. Sevov, *Inorg. Chem.* 40 (2001) 5361.
- [6] (a) S. Bobev, S.C. Sevov, *Inorg. Chem.* 39 (2000) 5930; (b) S. Bobev, S.C. Sevov, *Angew. Chem. Int. Ed.* 39 (2000) 4108.
- [7] B. Eisenmann, H. Schäfer, *Z. Anorg. Allg. Chem.* 403 (1974) 163.
- [8] A.K. Ganguli, J.D. Corbett, M. Köckerling, *J. Am. Chem. Soc.* 120 (1998) 1223.
- [9] (a) A.P. Wilkinson, C. Lind, R.A. Young, S.D. Shastri, P.L. Lee, G.S. Nolas, *Chem. Mater.* 14 (2002) 1300; (b) C.W. Myles, J.J. Dong, O.F. Sankey, *Phys. Rev. B* 64 (2001) Art. No. 165202; (c) S. Bobev, S.C. Sevov, *J. Solid State Chem.* 153 (2000) 92; (d) G.S. Nolas, B.C. Chakoumakos, B. Mahieu, G.J. Long, T.J.R. Weakley, *Chem. Mater.* 12 (2000) 1947; (e) G.S. Nolas, T.J.R. Weakley, J.L. Cohn, *Chem. Mater.* 11 (1999) 2470.
- [10] (a) M.L. Fornasini, G. Zanichchi, D. Mazzone, P. Riani, *Z. Kristallogr. NCS* 216 (2001) 21; (b) M.L. Fornasini, P. Manfrinetti, D. Mazzone, P. Riani, G. Zanichchi, *J. Solid State Chem.* 177 (2004) 1919; (c) A. Szytula, D. Fus, B. Penc, A. Jezierski, *J. Alloy Compd.* 317–318 (2001) 340; (d) W. Dörrscheidt, G. Savelsberg, J. Stöhr, H. Schäfer, *J. Less-Common Metals* 83 (1982) 269.
- [11] Z.-M. Sun, S.-Q. Xia, Y.-Z. Huang, L.-M. Wu, J.-G. Mao, *Inorg. Chem.* 44 (2005) 9242.
- [12] (a) W. Dörrscheidt, H. Schäfer, *J. Less-Common Metals* 58 (1978) 209; (b) P. Rahlfs, *Metallwirtschaft* 16 (1937) 640; (c) M. Boudard, B. Doisneau, F. Audebert, *J. Alloys Compd.* 370 (2004) 169; (d) D.A. Vennos, M.E. Badding, F.J. Disalvo, *J. Less-Common Metals* 175 (1991) 339.
- [13] (a) W. Dörrscheidt, G. Savelsberg, J. Stöhr, H. Schäfer, *J. Less-Common Metals* 83 (1982) 269; (b) A. Gil, B. Penc, S. Baran, J. Hernandez-Velasco, A. Szytula, A. Zygmunt, *J. Alloys Compd.* 361 (2003) 32; (c) P. Schobinger-Papamantellos, J. Rodriguez-Carvajal, G.H. Nieuwenhuys, L.W.F. Lemmens, K.H.J. Buschow, *J. Alloys Compd.* 262 (1997) 335; (d) P. Schobinger-Papamantellos, J. Rodriguez-Carvajal, H.F.J. Buschow, *J. Alloys Compd.* 240 (1996) 85.
- [14] (a) L.P. Komarovskaya, L.G. Aksel'drud, R.V. Skolozdra, *Kristallogr* 28 (1983) 1201; (b) L. Romaka, B. Penc, S. Baran, J. Leciejewicz, A. Szytula, N. Stüsser, J. Hernandez-Velasco, A. Zygmunt, *J. Alloys Compd.* 343 (2002) 66.
- [15] D. Rossi, R. Marazza, R. Ferro, *J. Less-Common Metals* 107 (1985) 99.

- [16] R.V. Skolozdra, V.M. Mandzyk, Yu.K. Gorelenko, V.D. Tkachuk, *Fiz. Met. Metalloved.* 52 (1981) 966.
- [17] (a) R.V. Skolozdra, L.G. Aksel'rud, O.E. Koretskaya, L.P. Komarovskaya, *Dopov. Akad. Nauk Ukr. RSR, Ser. B: Geol. Khim. Biol. Nauki* 1985 (1985) 24;
(b) R.V. Skolozdra, J.S. Mudryk, L.G. Aksel'rud, D. Fruchart, D. Gignoux, J. Pierre, *J. Alloys Compd.* 296 (2000) 303.
- [18] P. Schobinger-Papamantellos, G. Andre, J. Rodriguez-Carvajal, K.H.J. Buschow, L. Durivault, *J. Alloys Compd.* 325 (2001) 29.
- [19] (a) M.A. Zhuravleva, D. Bilc, S.D. Mahanti, M.G. Kanatzidis, *Z. Anorg. Allg. Chem.* 629 (2003) 327;
(b) L.P. Komarovskaya, R.V. Skolozdra, *Dopov. Akad. Nauk Ukr. RSR, Ser. A: Fiz.-Mat. Tekh. Nauki* 47 (1985) 81.
- [20] G.M. Zatorska, G.S. Dmytriv, V.V. Pavlyuk, E. Bartoszak-Adamska, M. Jaskolski, *J. Alloys Compd.* 346 (2002) 154.
- [21] (a) CrystalClear ver. 1. 3. 5. Rigaku Corp., Woodlands, TX, 1999;
(b) G.M. Sheldrick, SHELXTL, version 5.03, Siemens Analytical X-ray Instructuments, Madison, WI, 1995;
- (c) G.M. Sheldrick, SHELX-96 Program for Crystal Structure Determination, 1996.
- [22] J. Ren, W. Liang, M.-H. Whangbo, CAESAR for windows, Prime-Color Software, Inc., North Carolina State University, Raleigh, NC, 1998.
- [23] O.I. Bodak, E.I. Gladyshevskii, *Kristallogr* 14 (1969) 990.
- [24] J. Donohue, *The Structures of the Elements*, Wiley, New York, 1974.
- [25] (a) S. Cirafici, A. Palenzona, P. Manfrinetti, *J. Less-Common Metals* 90 (1983) 49;
(b) N. May, H. Schäfer, *Z. Naturforsch. B* 29 (1974) 20.
- [26] (a) A. Palenzona, P. Manfrinetti, M.L. Fornasini, *J. Alloys Compd.* 312 (2000) 165;
(b) F. Merlo, M.L. Fornasini, *J. Less-Common Metals* 13 (1967) 603.
- [27] B. Sieve, X. Chen, J. Cowen, P. Larson, S.D. Mahanti, M.G. Kanatzidis, *Chem. Mater.* 11 (1999) 2451.
- [28] J.H. Van Vleck, *The Theory of Electric and Magnetic Susceptibilities*, Oxford University Press, London, 1932, p. 248.
- [29] D. Kaczorowski, K. Gofryk, L. Romaka, Y. Mudryk, M. Konyk, P. Rogl, *Intermetallics* 13 (2005) 484.